

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET EFC4615R — General-Purpose Switching Device **Applications**

Features

- 2.5V drive
- · Best suited for LiB charging and discharging switch
- Common-drain type
- · Protection diode in
- Halogen free compliance

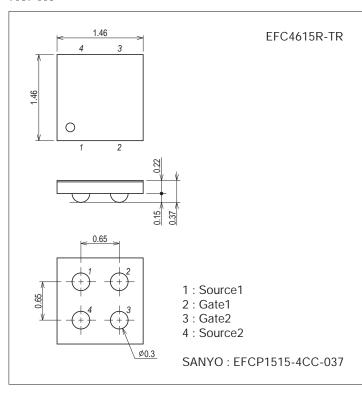
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Source-to-Source Voltage	VSSS		24	V
Gate-to-Source Voltage	VGSS		±12	V
Source Current (DC)	IS		6	A
Source Current (Pulse)	ISP	PW≤10μs, duty cycle≤1%	60	А
Total Dissipation	PT	When mounted on ceramic substrate (5000mm ² ×0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7067-001



Product & Package Information : EFCP

- Package
- JEITA, JEDEC
- Minimum Packing Quantity : 5,000 pcs./reel

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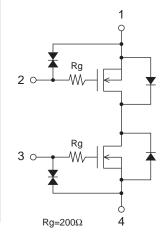
Marking

Taping Type : TR

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Electrical Connection



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91212 TKIM/62310PF TKIM TC-00002379 No. A1629-1/7

Electrical Characteristics at Ta=25°C

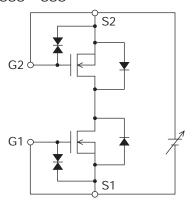
Parameter	Symbol	Conditions		Ratings			11
Parameter				min	typ	max	Unit
Source-to-Source Breakdown Voltage	V(BR)SSS	IS=1mA, VGS=0V	Test Circuit 1	24			V
Zero-Gate Voltage Source Current	ISSS	VSS=20V, VGS=0V	Test Circuit 1			1	μΑ
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VSS=0V	Test Circuit 2			±10	μΑ
Cutoff Voltage	VGS(off)	VSS=10V, IS=1mA	Test Circuit 3	0.5		1.3	V
Forward Transfer Admittance	yfs	VSS=10V, IS=3A	Test Circuit 4		5.4		S
	R _{SS} (on)1	IS=3A, VGS=4.5V	Test Circuit 5	19	27	31	mΩ
Statia Sauraa ta Sauraa On Stata Daalatanaa	R _{SS} (on)2	IS=3A, VGS=4.0V	Test Circuit 5	21	28	33	mΩ
Static Source-to-Source On-State Resistance	R _{SS} (on)3	IS=3A, VGS=3.1V	Test Circuit 5	24	33	44	mΩ
	RSS(on)4	IS=3A, VGS=2.5V	Test Circuit 5	28	39	52	mΩ
Turn-ON Delay Time	t _d (on)		Test Circuit 7		13		ns
Rise Time	tr				235		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.			335		ns
Fall Time	tf	1			360		ns
Total Gate Charge	Qg	VSS=10V, VGS=4.5V, IS=6A			8.8		nC
Forward Source-to-Source Voltage	VF(S-S)	I _S =6A, V _{GS} =0V Test Circuit 6			1	1.2	V

Ordering Information

Device	Package	Shipping	memo
EFC4615R-TR	EFCP	5,000pcs./reel	Pb Free and Halogen Free

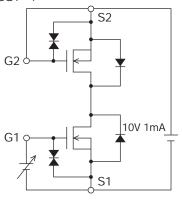
Test circuits are example of measuring FET1 side

Test Circuit 1 VSSS / ISSS

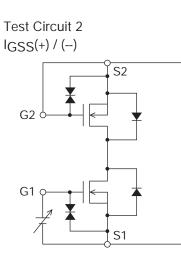


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Test Circuit 3 VGS(off)

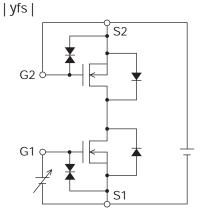


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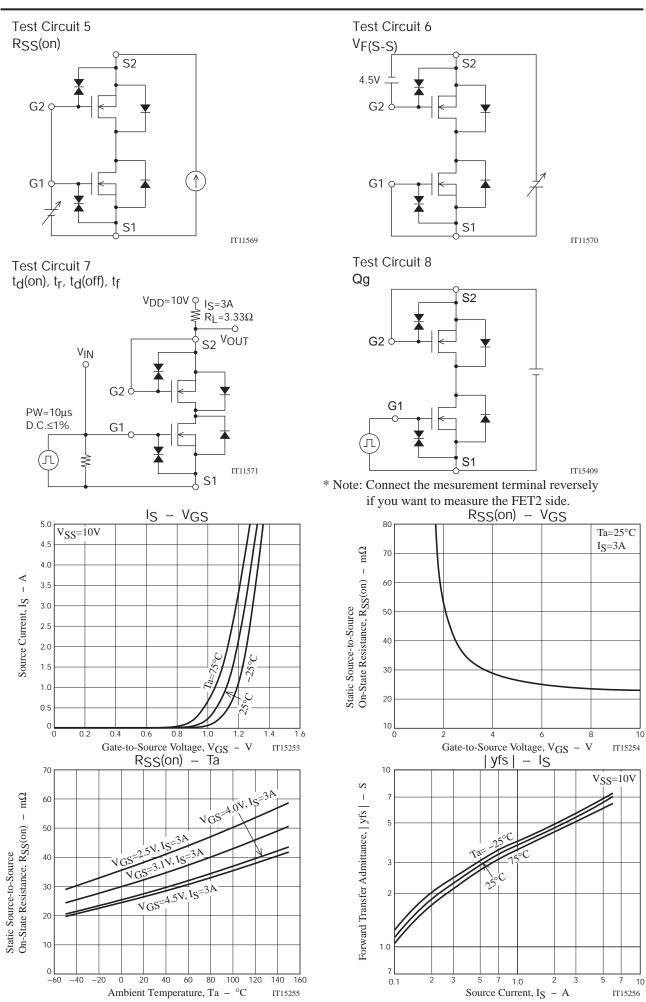
IT11566

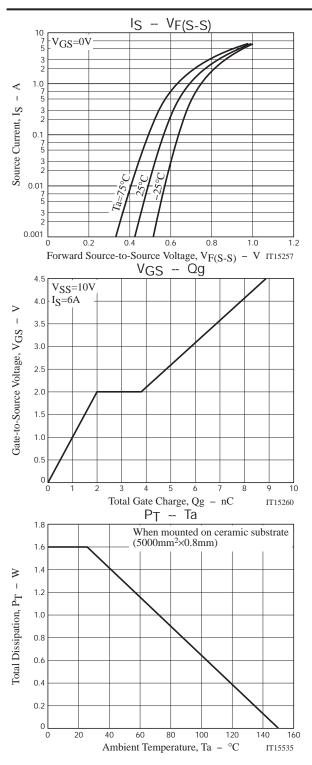
Test Circuit 4

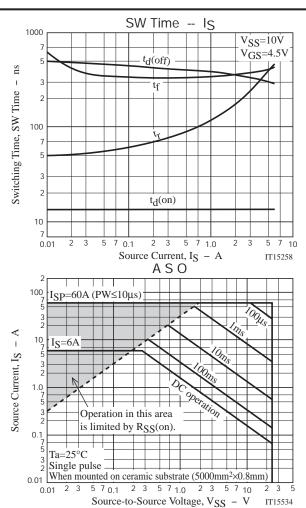


* Note: Connect the mesurement terminal reversely if you want to measure the FET2 side.

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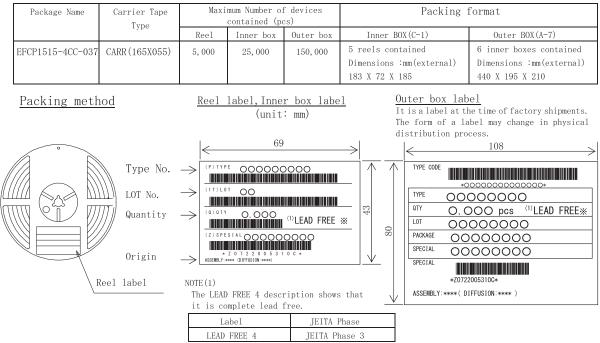




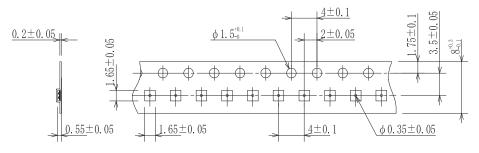


Taping Specification EFC4615R-TR

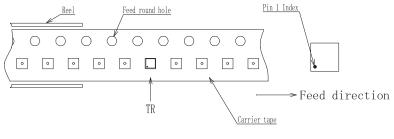
1. Packing Format



- 2. Taping configuration
 - 2-1. Carrier tape size (unit: mm)

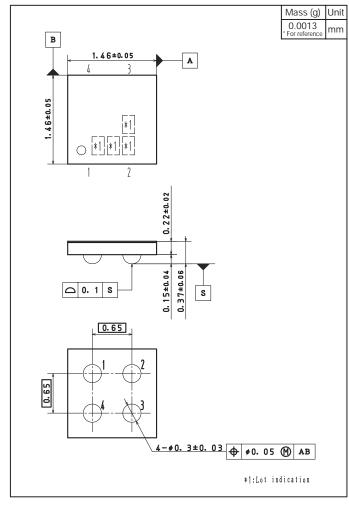


2-2. Device placement direction

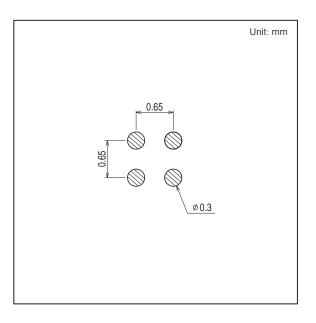


Packing type ····· TR

Outline Drawing EFC4615R-TR



Land Pattern Example



Note on usage : Since the EFC4615R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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